



N-Channel Enhancement-Mode Vertical DMOS FETs

Features

- ▶ Free from secondary breakdown
- ▶ Low power drive requirement
- ▶ Ease of paralleling
- ▶ Low C_{iss} and fast switching speeds
- ▶ Excellent thermal stability
- ▶ Integral source-drain diode
- ▶ High input impedance and high gain

Applications

- ▶ Motor controls
- ▶ Converters
- ▶ Amplifiers
- ▶ Switches
- ▶ Power supply circuits
- ▶ Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

General Description

The Supertex VN0550 is an enhancement-mode (normally-off) transistor that utilizes a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors, and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Device	Package	Wafer / Die Options		
		NW (Die in wafer form)	NJ (Die on adhesive tape)	ND (Die in waffle pack)
VN0550	VN0550N3-G	VN1550NW	VN1550NJ	VN1550ND

For packaged products, -G indicates package is RoHS compliant ('Green'). Devices in Wafer / Die form are RoHS compliant ('Green'). Refer to Die Specification VF15 for layout and dimensions.

Product Summary

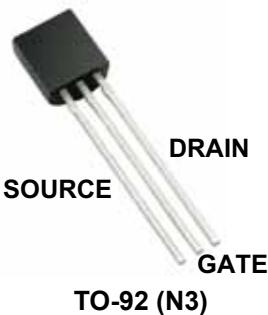
BV_{DSS}/BV_{DGS} (V)	$R_{DS(ON)}$ (max) (Ω)	$I_{D(ON)}$ (min) (mA)
500	60	150

Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV_{DSS}
Drain-to-gate voltage	BV_{DGS}
Gate-to-source voltage	$\pm 20V$
Operating and storage temperature	-55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Pin Configuration



Product Marking

SiVN
0 5 5 0
YYWW

YY = Year Sealed
WW = Week Sealed
____ = "Green" Packaging

Package may or may not include the following marks: Si or

TO-92 (N3)

Thermal Characteristics

Package	I_D (continuous) [†] (mA)	I_D (pulsed) (mA)	Power Dissipation @ $T_c = 25^\circ\text{C}$ (W)	θ_{jc} (°C/W)	θ_{ja} (°C/W)	I_{DR} [†] (mA)	I_{DRM} (mA)
TO-92	50	250	1.0	125	170	50	250

Notes:

[†] I_D (continuous) is limited by max rated T_j .

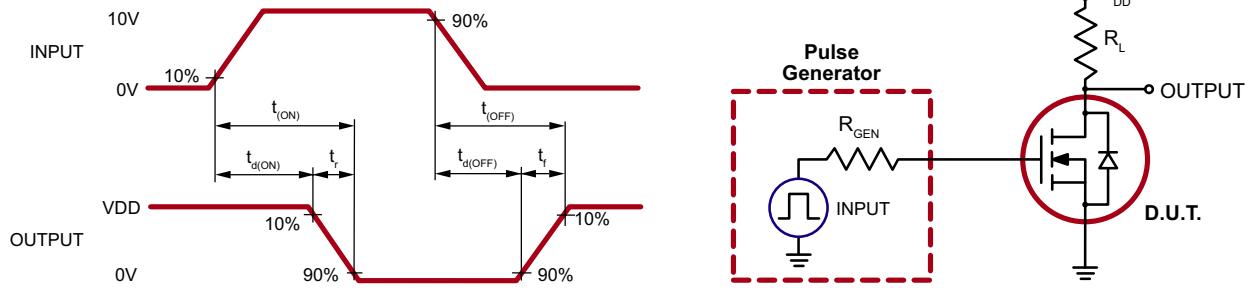
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Sym	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSS}	Drain-to-source breakdown voltage	500	-	-	V	$V_{GS} = 0\text{V}$, $I_D = 1.0\text{mA}$
$V_{GS(\text{th})}$	Gate threshold voltage	2.0	-	4.0	V	$V_{GS} = V_{DS}$, $I_D = 1.0\text{mA}$
$\Delta V_{GS(\text{th})}$	Change in $V_{GS(\text{th})}$ with temperature	-	-3.8	-5.0	mV/°C	$V_{GS} = V_{DS}$, $I_D = 1.0\text{mA}$
I_{GSS}	Gate body leakage current	-	-	100	nA	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$
I_{DSS}	Zero gate voltage drain current	-	-	10	μA	$V_{GS} = 0\text{V}$, V_{DS} = Max Rating
		-	-	1.0	mA	$V_{DS} = 0.8$ Max Rating, $V_{GS} = 0\text{V}$, $T_A = 125^\circ\text{C}$
$I_{D(\text{ON})}$	On-state drain current	-	100	-	mA	$V_{GS} = 5.0\text{V}$, $V_{DS} = 25\text{V}$
		150	350	-		$V_{GS} = 10\text{V}$, $V_{DS} = 25\text{V}$
$R_{DS(\text{ON})}$	Static drain-to-source on-state resistance	-	45	-	Ω	$V_{GS} = 5.0\text{V}$, $I_D = 50\text{mA}$
		-	40	60		$V_{GS} = 10\text{V}$, $I_D = 50\text{mA}$
$\Delta R_{DS(\text{ON})}$	Change in $R_{DS(\text{ON})}$ with temperature	-	1.0	1.7	%/°C	$V_{GS} = 10\text{V}$, $I_D = 50\text{mA}$
G_{FS}	Forward transconductance	50	100	-	mmho	$V_{DS} = 25\text{V}$, $I_D = 50\text{mA}$
C_{ISS}	Input capacitance	-	45	55	pF	$V_{GS} = 0\text{V}$,
C_{OSS}	Common source output capacitance	-	8.0	10		$V_{DS} = 25\text{V}$,
C_{RSS}	Reverse transfer capacitance	-	2.0	5.0		$f = 1.0\text{MHz}$
$t_{d(\text{ON})}$	Turn-on time	-	-	10	ns	$V_{DD} = 25\text{V}$, $I_D = 150\text{mA}$, $R_{GEN} = 25\Omega$
t_r	Rise time	-	-	15		
$t_{d(\text{OFF})}$	Turn-off time	-	-	10		
t_f	Fall time	-	-	10		
V_{SD}	Diode forward voltage drop	-	0.8	-	V	$V_{GS} = 0\text{V}$, $I_{SD} = 500\text{mA}$
t_{rr}	Reverse recovery time	-	300	-	ns	$V_{GS} = 0\text{V}$, $I_{SD} = 500\text{mA}$

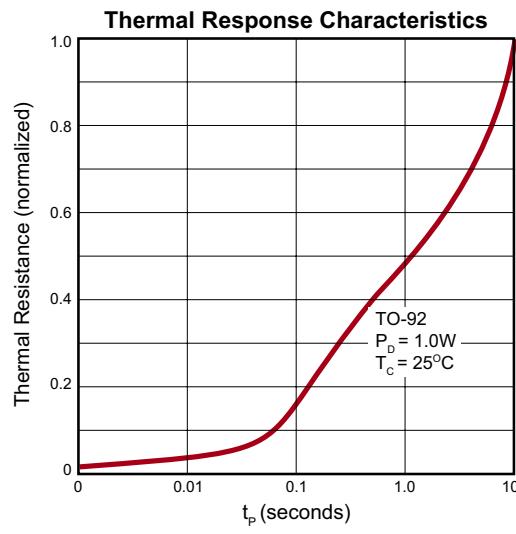
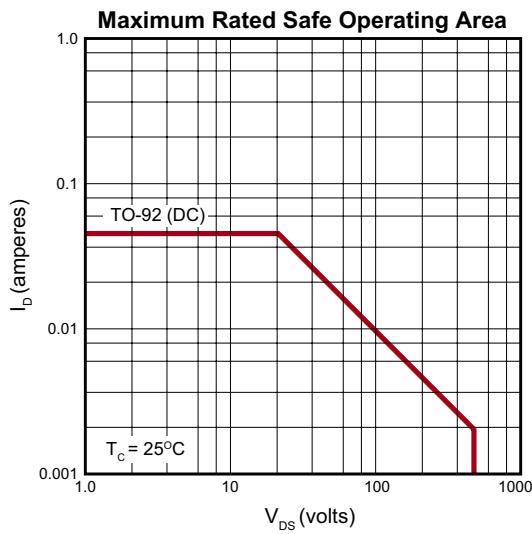
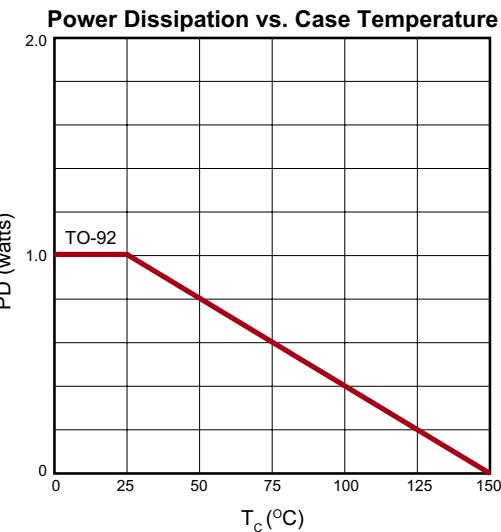
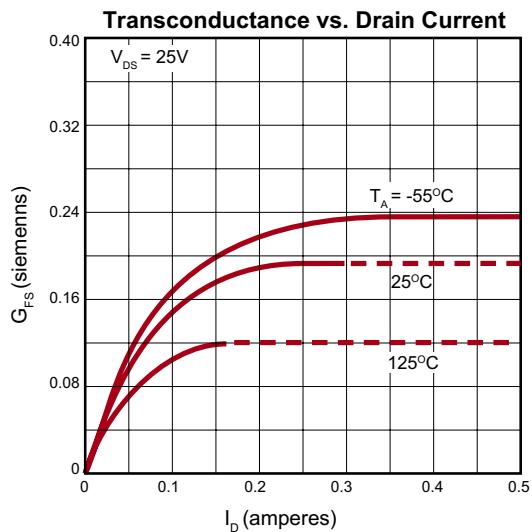
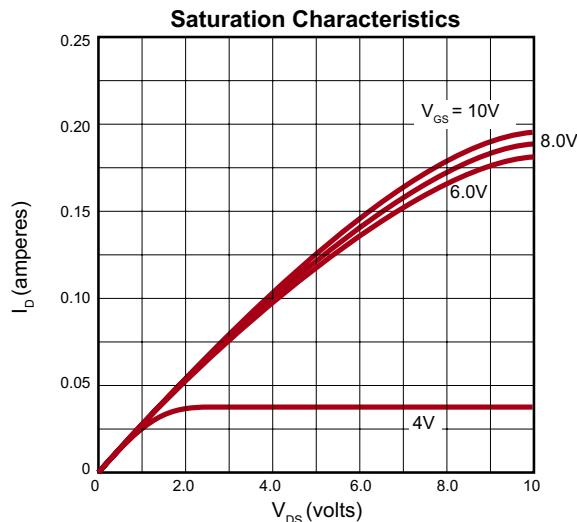
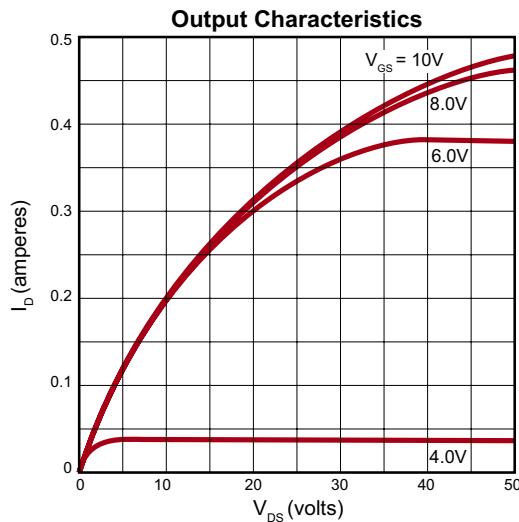
Notes:

- All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: $300\mu\text{s}$ pulse, 2% duty cycle.)
- All A.C. parameters sample tested.

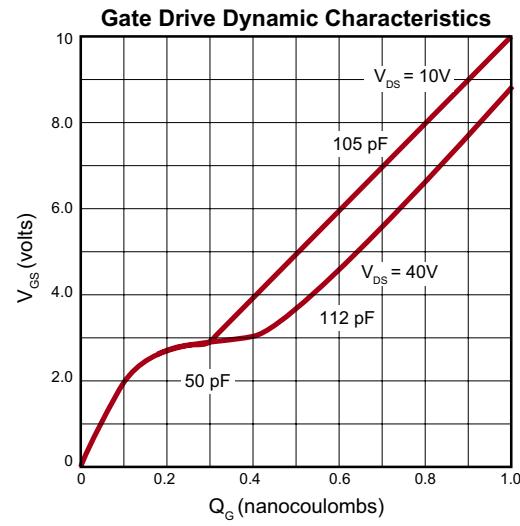
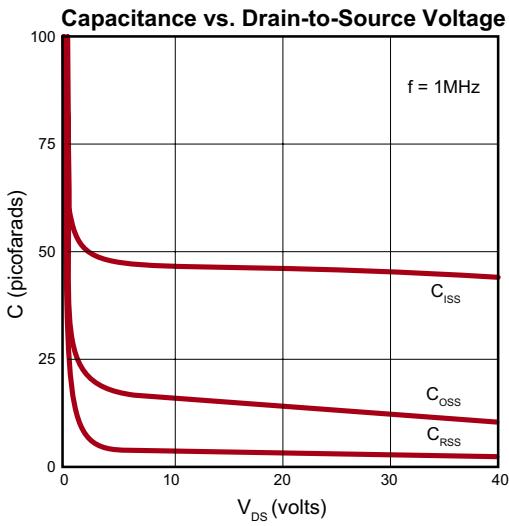
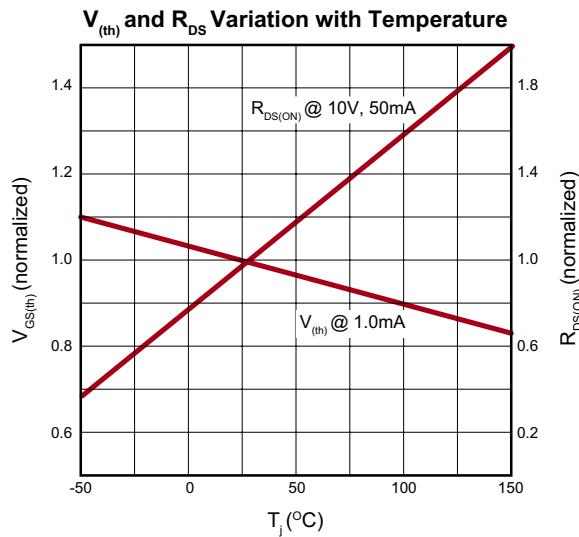
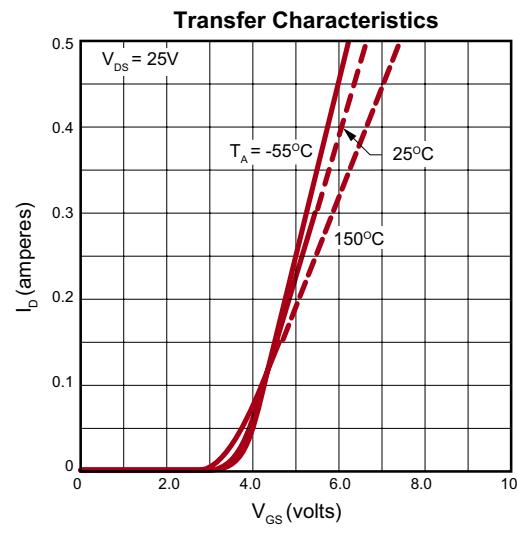
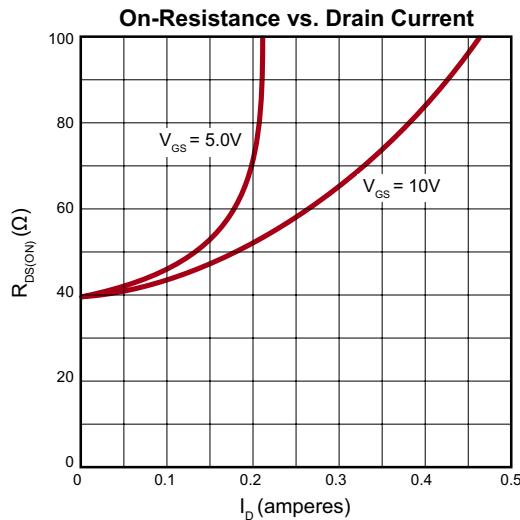
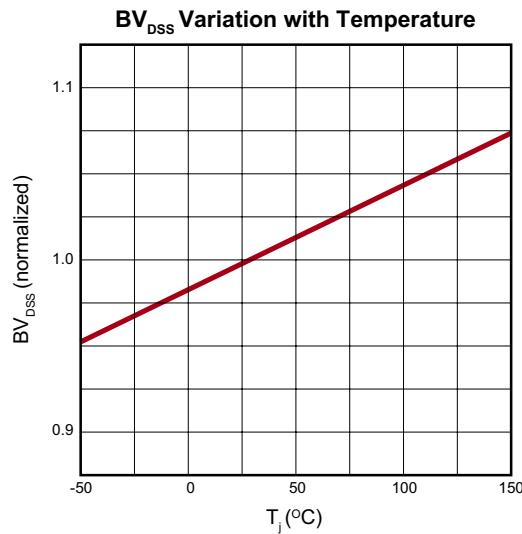
Switching Waveforms and Test Circuit



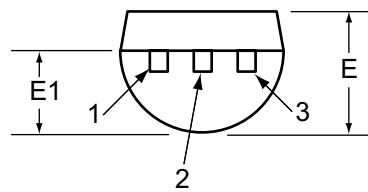
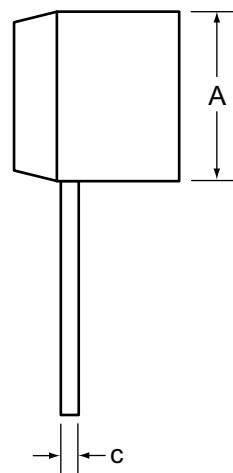
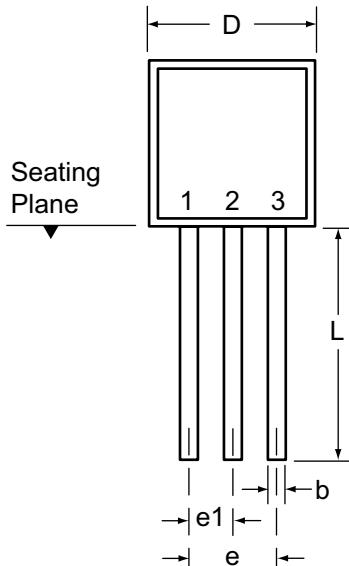
Typical Performance Curves



Typical Performance Curves (cont.)



3-Lead TO-92 Package Outline (N3)



Symbol		A	b	c	D	E	E1	e	e1	L
Dimensions (inches)	MIN	.170	.014 [†]	.014 [†]	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022 [†]	.022 [†]	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.

* This dimension is not specified in the JEDEC drawing.

† This dimension differs from the JEDEC drawing.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO92N3, Version E041009.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <http://www.supertex.com/packaging.html>.)

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ООО "ЛайфЭлектроникс"

"LifeElectronics" LLC

ИНН 7805602321 КПП 780501001 Р/С 40702810122510004610 ФАКБ "АБСОЛЮТ БАНК" (ЗАО) в г.Санкт-Петербурге К/С 30101810900000000703 БИК 044030703

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С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибуторских договоров

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- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помочь разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



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